

EE203 LAB3 Biasing a FET Transistor

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EQUIPMENT :

A voltage source, voltmeters, a laboratory lead kit A signal generator and an oscilloscope

OBJECTIVE :

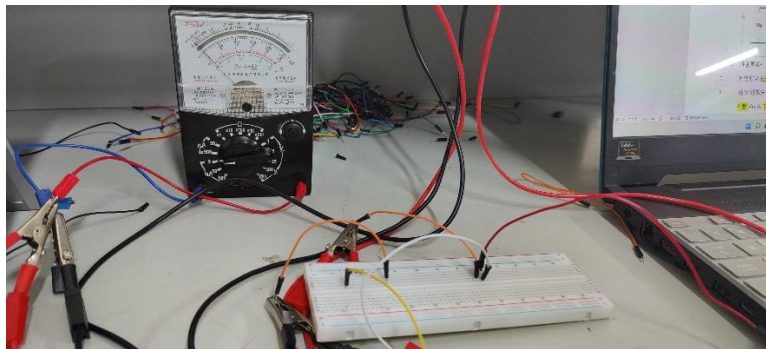
The purpose of this experiment is to demonstrate various biasing techniques for FET transistors

Part1

For PMOS

We measure that V_{in} is 1.99V,

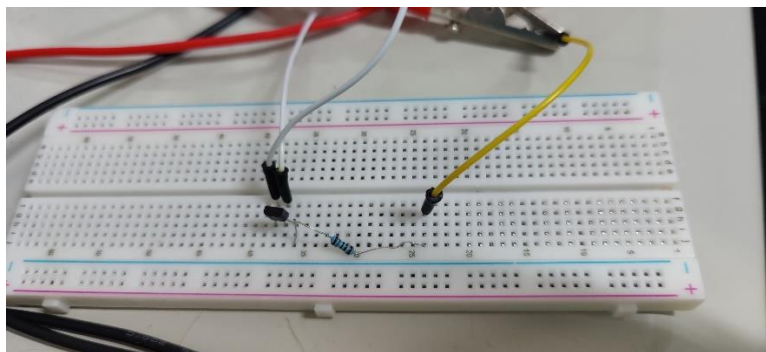
so $V_t = V_{gs} = -V_{sg} = V_{in} - 5 = -3.01V$



For NMOS

We measure that V_{in} is 1.96V,

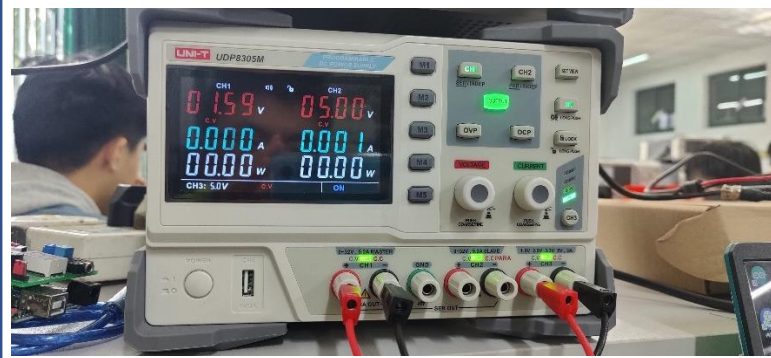
so $V_t = V_g = V_{in} = 1.96V$



\therefore PMOS $V_t = -3.01V$, NMOS $V_t = 1.96V$

Part2

For PMOS



We measure that when V_{in} is 1.59, the V_{out} is 2.5V

$$V_{gs} = -V_{sg} = V_{in} - 5 = -3.41V$$

$$V_{gs} - V_t = -0.4V$$

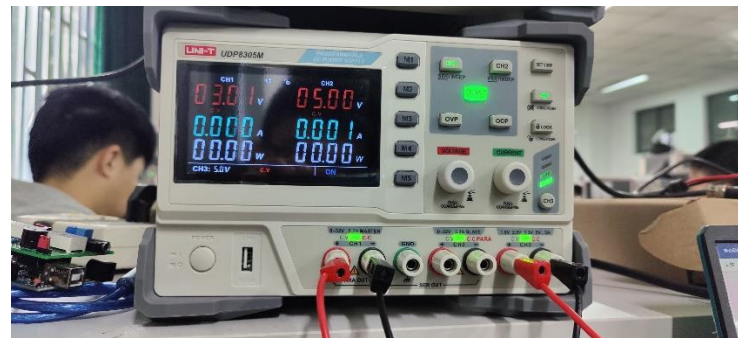
So

$$V_{ds} = V_{out} - 0 = 2.5V$$

$V_{ds} > V_{gs} - V_t$, This equation is true

So it meets the formula, we verify it is in saturation

For NMOS



We measure that when V_{in} is 3.01, the V_{out} is 2.5V

$$V_{gs} = V_{in} = 3.01V$$

$$V_{gs} - V_t = 1.05V$$

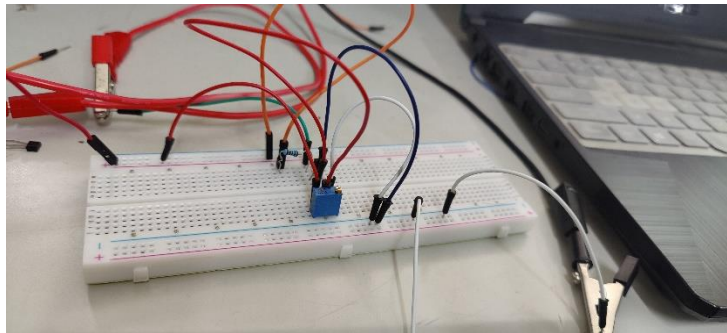
So

$$V_{ds} = V_{out} - 0 = 2.5V$$

$V_{ds} > V_{gs} - V_t$, This equation is true

So it meets the formula, we verify it is in saturation

PART3



We measure that when $R_{bias1}=831\Omega$, $R_{bias2}=1212\Omega$, we could make $V_{out}=2.5V$.
So the ratio of two resistances is $R_{bias1}/R_{bias2}=1212\Omega/831\Omega=1.46$

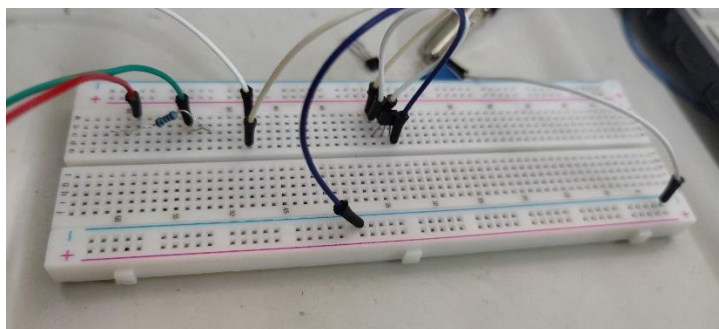
the ratio of divider resistance is 1.46

Would there be any benefit to going for very small resistors as compared to very big resistors?

Because the resistance between GS is not infinite actually, so we could use a small resistor. It would minimize error.

Gate resistance is small, switching device on and off fast, small switching loss; Otherwise, it is slow and the switching loss is large.

PART4



We measure $I_{ds}=2.7mA$

$V_{out}=5V - I_{ds} R = 2.3V$

then, $V_{ds}=V_{out}-0=2.3V$

So the equivalent resistance of MOS is $V_{ds}/I_{ds}=851.85\Omega$

For this Drain-feedback biasing model. The voltage of THE VDD will be partially applied to the G terminal to achieve the effect of controlling the V_{gs} .

Summary

We successfully construct the circuit, and measure values that we want. Then we calculate the V_t of NMOS and PMOS.

We also set two biasing approaches to finish the required tasks:

We use resistor divider correctly and get the ratio of two resistance.

We set Drain-feedback biasing model, we successfully get the equivalent resistance.